

# David J Lockwood

## List of Publications by Year in descending order

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132  
papers

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citations

218677

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118850

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135  
all docs

135  
docs citations

135  
times ranked

4596  
citing authors

#	ARTICLE	IF	CITATIONS
1	Nickel hydroxides and related materials: a review of their structures, synthesis and properties. Proceedings of the Royal Society A: Mathematical, Physical and Engineering Sciences, 2015, 471, 20140792.	2.1	610
2	Quantum Confined Luminescence in Si/SiO <sub>2</sub> Superlattices. Physical Review Letters, 1996, 76, 539-541.	7.8	430
3	Raman and Infrared Spectroscopy of $\hat{\Gamma}_\pm$ and $\hat{\Gamma}_2'$ Phases of Thin Nickel Hydroxide Films Electrochemically Formed on Nickel. Journal of Physical Chemistry A, 2012, 116, 6771-6784.	2.5	293
4	Nanocrystalline-silicon superlattice produced by controlled recrystallization. Applied Physics Letters, 1998, 72, 43-45.	3.3	243
5	Quantum confinement in Si and Ge nanostructures: Theory and experiment. Applied Physics Reviews, 2014, 1, 011302.	11.3	167
6	Quantum confinement in Si and Ge nanostructures. Journal of Applied Physics, 2012, 111, .	2.5	158
7	Folded acoustic phonons in Si/Ge <sub>x</sub> Si <sub>1-x</sub> strained-layer superlattices. Physical Review B, 1987, 35, 2243-2251.	3.2	132
8	Spin Waves in Nickel Nanorings of Large Aspect Ratio. Physical Review Letters, 2005, 94, 137208.	7.8	126
9	Optical phonon frequencies and damping in AlAs, GaP, GaAs, InP, InAs and InSb studied by oblique incidence infrared spectroscopy. Solid State Communications, 2005, 136, 404-409.	1.9	115
10	Ge dots and nanostructures grown epitaxially on Si. Journal of Physics Condensed Matter, 2006, 18, R139-R174.	1.8	104
11	Applications of in Situ Raman Spectroscopy for Identifying Nickel Hydroxide Materials and Surface Layers during Chemical Aging. ACS Applied Materials & Interfaces, 2014, 6, 3141-3149.	8.0	90
12	Strain in coherent-wave SiGe/Si superlattices. Solid State Communications, 2000, 114, 505-510.	1.9	85
13	Magnon Squeezing in an Antiferromagnet: Reducing the Spin Noise below the Standard Quantum Limit. Physical Review Letters, 2004, 93, 107203.	7.8	85
14	Silicon-Germanium Nanostructures for Light Emitters and On-Chip Optical Interconnects. Proceedings of the IEEE, 2009, 97, 1284-1303.	21.3	78
15	Ion Pair Formation in NaNO <sub>3</sub> /D <sub>2</sub> O Solutions: Raman and Infrared Spectra, Partial Molal Volumes, Conductance, and Viscosity. Canadian Journal of Chemistry, 1972, 50, 2951-2962.	1.1	55
16	Magnon squeezing in antiferromagnetic MnF <sub>2</sub> and FeF <sub>2</sub> . Physical Review B, 2006, 73, .	3.2	55
17	Coexistence of fast and slow luminescence in three-dimensional Si <sup>δ+</sup> -Si <sup>δ-</sup> <sub>x</sub> Ge <sub>x</sub> nanostructures. Physical Review B, 2005, 72, .	3.2	50
18	Formation of colloidal alloy semiconductor CdTeSe magic-size clusters at room temperature. Nature Communications, 2019, 10, 1674.	12.8	49

#	ARTICLE	IF	CITATIONS
19	Photoluminescence and Raman scattering in three-dimensional Si/Si <sup>x</sup> Ge <sub>1-x</sub> nanostructures. Applied Physics Letters, 2004, 84, 1293-1295.	3.3	45
20	Optical phonons in Al <sub>x</sub> Ga <sub>1-x</sub> As: Raman spectroscopy. Physical Review B, 2004, 70, .	3.2	40
21	Light emission in silicon nanostructures. Journal of Materials Science: Materials in Electronics, 2009, 20, 235-244.	2.2	38
22	Disorder and the optical properties of amorphous silicon grown by molecular beam epitaxy. Solid State Communications, 2001, 120, 429-434.	1.9	35
23	Stabilized porous silicon optical superlattices with controlled surface passivation. Applied Physics Letters, 2008, 93, 061113.	3.3	34
24	Lattice dynamics of the ordered vacancy compound HgIn <sub>2</sub> Square Operator Te <sub>4</sub> . Journal of Physics C: Solid State Physics, 1976, 9, 2997-3011.	1.5	31
25	Optical dispersion relationships in amorphous silicon grown by molecular beam epitaxy. Journal of Non-Crystalline Solids, 2001, 290, 57-63.	3.1	31
26	Polarized Raman scattering and localized embedded strain in self-organized Si/Ge nanostructures. Applied Physics Letters, 2003, 83, 5035-5037.	3.3	27
27	Depth-dependent disordering in a-Si produced by self-ion-implantation. Physical Review B, 1994, 50, 17080-17084.	3.2	26
28	Spin waves in permalloy nanowires: The importance of easy-plane anisotropy. Physical Review B, 2006, 73, .	3.2	26
29	Resonant tunneling in partially disordered silicon nanostructures. Europhysics Letters, 2001, 55, 552-558.	2.0	25
30	Raman and transmission electron microscopy study of disordered silicon grown by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 943.	2.1	25
31	Bovine serum albumin adsorption on passivated porous silicon layers. Canadian Journal of Chemistry, 2004, 82, 1545-1553.	1.1	25
32	Raman spectrum of AgGaS <sub>2</sub> . Journal of Physics C: Solid State Physics, 1975, 8, 3241-3250.	1.5	24
33	Spin relaxation in quantum dots with random spin-orbit coupling. Physical Review B, 2005, 72, .	3.2	24
34	Raman scattering from the 1D antiferromagnets RbCoCl <sub>3</sub> and RbNiCl <sub>3</sub> . Journal of Physics C: Solid State Physics, 1983, 16, 6451-6474.	1.5	23
35	Role of quantum confinement in luminescence efficiency of group IV nanostructures. Journal of Applied Physics, 2014, 115, .	2.5	22
36	Optical absorption in an amorphous silicon superlattice grown by molecular beam epitaxy. Solid State Communications, 2002, 122, 271-275.	1.9	21

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37	Electronic Raman scattering in quantum dots revisited. <i>Solid State Communications</i> , 2005, 135, 554-562.	1.9	20
38	Probing the composition of Ge dots and Si <sup>1-x</sup> Ge <sup>x</sup> island superlattices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006, 24, 663-667.	2.1	20
39	Raman scattering in Si/SiGe nanostructures: Revealing chemical composition, strain, intermixing, and heat dissipation. <i>Journal of Applied Physics</i> , 2014, 116, .	2.5	20
40	Ultrafast carrier dynamics and the role of grain boundaries in polycrystalline silicon thin films grown by molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 2016, 31, 105017.	2.0	20
41	Spin-phonon interaction in transition-metal difluoride antiferromagnets: Theory and experiment. <i>Low Temperature Physics</i> , 2019, 45, 78-91.	0.6	19
42	Influence of growth temperature on order within silicon films grown by ultrahigh-vacuum evaporation on silica. <i>Applied Physics Letters</i> , 2006, 88, 121920.	3.3	18
43	Physical properties of lanthanum monosulfide thin films grown on (100) silicon substrates. <i>Journal of Applied Physics</i> , 2006, 99, 123502.	2.5	18
44	Anomalous phonon intensities in the Raman spectrum of disordered CsMg <sup>1-x</sup> CoxCl <sub>3</sub> . <i>Solid State Communications</i> , 1981, 39, 395-400.	1.9	17
45	Patchwork field emission properties of lanthanum monosulfide thin films. <i>Journal of Vacuum Science &amp; Technology B</i> , 2006, 24, 2412.	1.3	17
46	An amorphous-to-crystalline phase transition within thin silicon films grown by ultra-high-vacuum evaporation and its impact on the optical response. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	17
47	Low-temperature Si growth on Si (001): Impurity incorporation and limiting thickness for epitaxy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004, 22, 1479.	1.6	16
48	Advances in the growth and characterization of Ge quantum dots and islands. <i>Journal of Materials Research</i> , 2005, 20, 3278-3293.	2.6	16
49	Phonon-assisted optical absorption in germanium. <i>Physical Review B</i> , 2018, 98, .	3.2	16
50	Influence of interchain coupling on the one-dimensional magnon Raman spectrum of CsCoBr <sub>3</sub> . <i>Solid State Communications</i> , 1980, 36, 593-597.	1.9	15
51	Pulsed laser deposition of lanthanum monosulfide thin films on silicon substrates. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 318.	1.6	15
52	Structural and optical properties of three-dimensional Si <sup>1-x</sup> Ge <sup>x</sup> /Si nanostructures. <i>Semiconductor Science and Technology</i> , 2008, 23, 064003.	2.0	15
53	Carrier tunneling in nanocrystalline silicon/silicon dioxide superlattices: A weak coupling model. <i>Physical Review B</i> , 2004, 69, .	3.2	14
54	Peculiarities of the structural phase transitions in Na <sub>2</sub> SO <sub>4</sub> (V): a Raman scattering study. <i>Journal of Physics Condensed Matter</i> , 2005, 17, 6095-6108.	1.8	14

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55	In situ monitoring of protein adsorption on functionalized porous Si surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 747-751.	2.1	14
56	Resonant indirect optical absorption in germanium. Physical Review B, 2017, 96, .	3.2	14
57	Photoluminescence of Ge nanocrystals self-assembled on SiO <sub>2</sub> . Superlattices and Microstructures, 2008, 44, 305-314.	3.1	13
58	Magnetic-field dependence of spin waves in ordered permalloy nanowire arrays in two dimensions. Journal of Applied Physics, 2005, 98, 046103.	2.5	12
59	Polarons in electron-populated quantum dots revealed by resonant Raman scattering. Physical Review B, 2006, 73, .	3.2	12
60	Photoluminescence and Raman scattering in axial Si/Ge nanowire heterojunctions. Applied Physics Letters, 2009, 95, 133120.	3.3	12
61	Photoluminescence Efficiency of Self-Assembled Ge Nanocrystals. Journal of the Electrochemical Society, 2009, 156, H913.	2.9	11
62	The nonlinear Rashba effect in Hg <sub>0.77</sub> Cd <sub>0.23</sub> Te inversion layers probed by weak antilocalization analysis. Journal of Applied Physics, 2013, 113, .	2.5	11
63	(Invited) Photoluminescence Efficiency of Germanium Dots Self-Assembled on Oxides. ECS Transactions, 2013, 53, 185-206.	0.5	11
64	High intensity and oscillatory electroluminescence observed during porous etching of GaP in HBr and HF electrolytes. Chemical Physics Letters, 2005, 414, 47-50.	2.6	10
65	Characterization and field emission properties of lanthanum monosulfide nanoprotusion arrays obtained by pulsed laser deposition on self-assembled nanoporous alumina templates. Journal of Applied Physics, 2007, 101, 235101.	1.3	10
66	Crossing and anticrossing of spin-split Landau levels in an Al <sub>x</sub> Ga <sub>1-x</sub> As <sub>z</sub> Ge <sub>1-z</sub> heterostructure. Physical Review B, 2007, 76, .	3.2	10
67	CoF <sub>2</sub> nanowires: Synthesis, growth, and properties. Physical Review B, 2007, 76, .	3.2	10
68	Fast light-emitting silicon-germanium nanostructures for optical interconnects. Optical and Quantum Electronics, 2012, 44, 505-512.	3.3	10
69	Structural and optical properties of axial silicon-germanium nanowire heterojunctions. Journal of Applied Physics, 2015, 118, .	2.5	10
70	Influence of interface potential on the effective mass in Ge nanostructures. Journal of Applied Physics, 2015, 117, .	2.5	10
71	Light scattering from electronic and magnetic excitations in transition-metal halides. Topics in Applied Physics, 1982, , 59-92.	0.8	9
72	Silicon-germanium nanostructures for on-chip optical interconnects. Applied Physics A: Materials Science and Processing, 2009, 95, 1015-1027.	2.3	9

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73	Optical phonons via oblique-incidence infrared spectroscopy and their deformation potentials in $\text{In}_{1-x}\text{Ga}_x\text{As}$ . <i>Journal of Applied Physics</i> , 2007, 101, 113524.	2.5	8
74	Predicting Size Distributions of Ge Nanodots from Their Photoluminescence. <i>Journal of the Electrochemical Society</i> , 2010, 157, H1160.	2.9	8
75	Review Article: Rare-earth monosulfides as durable and efficient cold cathodes. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011, 29, 06F602.	1.2	8
76	Excitation wavelength dependent photoluminescence in structurally non-uniform Si/SiGe-island heteroepitaxial multilayers. <i>Journal of Applied Physics</i> , 2012, 111, 114313.	2.5	8
77	Magneto-optic coupling coefficients for one- and two-magnon Raman scattering in rutile-structure antiferromagnets $\text{FeF}_2$ , $\text{MnF}_2$ , $\text{CoF}_2$ , and $\text{NiF}_2$ . <i>Low Temperature Physics</i> , 2012, 38, 549-558.	0.6	8
78	Si/SiGe Heterointerfaces in One-, Two-, and Three-Dimensional Nanostructures: Their Impact on SiGe Light Emission. <i>Frontiers in Materials</i> , 2016, 3, .	2.4	8
79	Raman scattering from magnons and excitons in the $\sqrt{3}\sqrt{3}$ ordered phases of $\text{CsCoBr}_3$ . <i>Journal of Applied Physics</i> , 1982, 53, 8169-8171.	2.5	7
80	Phonons in strained $\text{In}_{1-x}\text{Ga}_x\text{As}/\text{InP}$ epilayers characterized by infrared reflectance. <i>Applied Physics Letters</i> , 2005, 86, 221904.	3.3	7
81	Organic monolayers detected by single reflection attenuated total reflection infrared spectroscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006, 24, 668-672.	2.1	7
82	Compositional Redistribution in Coherent $\text{Si}_{1-x}\text{Ge}_x$ Islands on Si(100). <i>IEEE Nanotechnology Magazine</i> , 2007, 6, 245-249.	2.0	7
83	Photoluminescence Efficiency and Size Distribution of Self Assembled Ge Dots on Porous $\text{TiO}_2$ . <i>Journal of Nanoscience and Nanotechnology</i> , 2011, 11, 9190-9195.	0.9	7
84	Fast and intense photoluminescence in a SiGe nano-layer embedded in multilayers of Si/SiGe clusters. <i>Applied Physics Letters</i> , 2013, 103, 033103.	3.3	7
85	Selection and jump rules in electronic Raman scattering from $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ artificial atoms. <i>Physical Review B</i> , 2005, 71, .	3.2	5
86	Optical phonons in $\text{InP}_{1-x}\text{As}_x$ revisited. <i>Journal of Applied Physics</i> , 2007, 102, .	2.5	5
87	Exact diagonalization studies of inelastic light scattering in self-assembled quantum dots. <i>Physical Review B</i> , 2009, 79, .	3.2	5
88	Selective growth and ordering of SiGe nanowires for band gap engineering. <i>Nanotechnology</i> , 2014, 25, 335303.	2.6	5
89	Light Emission in Silicon Nanostructures. , 1998, , 185-209.		5
90	Optical Properties of Composition-Controlled Three-Dimensional $\text{Si}_{1-x}\text{Ge}_x$ Nanostructures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2006, 12, 1579-1584.	2.9	4

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91	Infrared spectroscopy of self-assembled monolayer films on silicon. <i>Surface Science</i> , 2007, 601, 2566-2570.	1.9	4
92	Field emission properties of metallic nanostructures self-assembled on nanoporous alumina and silicon templates. <i>Journal of Vacuum Science &amp; Technology B</i> , 2008, 26, 885-890.	1.3	4
93	Three-Dimensional Silicon-Germanium Nanostructures for CMOS Compatible Light Emitters and Optical Interconnects. <i>Advances in Optical Technologies</i> , 2008, 2008, 1-16.	0.8	4
94	Strain-induced lateral self-organization in Si/SiO <sub>2</sub> nanostructures. <i>Applied Physics Letters</i> , 2010, 96, 013105.	3.3	4
95	Photoluminescence fatigue in three-dimensional silicon/silicon-germanium nanostructures. <i>Journal of Applied Physics</i> , 2012, 111, 064318.	2.5	4
96	Bright photoluminescence from ordered arrays of SiGe nanowires grown on Si(111). <i>Beilstein Journal of Nanotechnology</i> , 2014, 5, 2498-2504.	2.8	4
97	Fast Light-Emitting Silicon-Germanium Nanostructures. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2014, 20, 225-231.	2.9	4
98	Strained HgTe plates grown on SrTiO <sub>3</sub> investigated by micro-Raman mapping. <i>Journal of Applied Physics</i> , 2016, 120, 115304.	2.5	4
99	Editors' Choice "Optical Emission from Germanium Nanocrystals. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, R195-R205.	1.8	4
100	Photoluminescence in PbS nanocrystal thin films: Nanocrystal density, film morphology and energy transfer. <i>Journal of Applied Physics</i> , 2020, 128, 134301.	2.5	4
101	One- and two-magnon Raman scattering in the canted antiferromagnet NiF <sub>2</sub> . <i>Journal of Magnetism and Magnetic Materials</i> , 2007, 310, 1593-1595.	2.3	3
102	Field emission from lanthanum monosulfide thin films grown on the (100) magnesium oxide substrates. <i>Journal of Vacuum Science &amp; Technology B</i> , 2008, 26, 891-897.	1.3	3
103	Self-assembled silicon-germanium nanostructures for CMOS compatible light emitters. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2870-2874.	0.8	3
104	Disorder and defect formation mechanisms in molecular-beam-epitaxy grown silicon epilayers. <i>Thin Solid Films</i> , 2013, 527, 38-44.	1.8	3
105	The effective g-factor in In <sub>0.53</sub> Ga <sub>0.47</sub> As/In <sub>0.52</sub> Al <sub>0.48</sub> As quantum well investigated by magnetotransport measurement. <i>Journal of Applied Physics</i> , 2013, 113, 033704.	2.5	3
106	Oblique incidence infrared reflectance spectroscopy of phonons in cubic MgO, MnO, and NiO. <i>Infrared Physics and Technology</i> , 2020, 109, 103405.	2.9	3
107	Pore formation on p-type InP(100). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 1446-1450.	1.8	2
108	Field Emission from Self-Assembled Arrays of Lanthanum Monosulfide Nanoprotrusions. <i>Journal of Nanomaterials</i> , 2008, 2008, 1-4.	2.7	2

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109	Photoluminescence and Raman spectral study of C incorporation in strained Si <sub>1-x</sub> Ge <sub>x</sub> epilayers on Si(100). Journal of Applied Physics, 2008, 103, 063513.	2.5	2
110	Quantum confinement in Si and Ge nanostructures: effect of crystallinity. , 2013, , .		2
111	Carrier recombination in tailored multilayer Si/Si <sub>1-x</sub> Ge <sub>x</sub> nanostructures. Physica B: Condensed Matter, 2014, 453, 29-33.	2.7	2
112	Influence of the growth temperature on the spectral dependence of the optical functions associated with thin silicon films grown by ultra-high-vacuum evaporation on optical quality fused quartz substrates. Journal of Materials Science: Materials in Electronics, 2020, 31, 13186-13198.	2.2	2
113	(Invited) Germanium Nanocrystal Luminescence: Spectral and Spatial Variations. ECS Transactions, 2020, 97, 3-13.	0.5	2
114	Circular dichroism and Raman optical activity in antiferromagnetic transition-metal fluorides. Low Temperature Physics, 2005, 31, 786-793.	0.6	1
115	Electronic Raman scattering from holes in InAs/GaAs self-assembled quantum dots. Electronics Letters, 2007, 43, 1162.	1.0	1
116	Photoluminescence of strained Si <sub>1-x</sub> Ge <sub>x</sub> epilayers on Si(100). Thin Solid Films, 2008, 517, 128-131.	1.8	1
117	Field emission characteristics of a lanthanum monosulfide cold cathode array fabricated using microelectromechanical systems technology. Journal of Vacuum Science & Technology B, 2008, 26, 764-769.	1.3	1
118	Direct Observation of Polarons in Electron Populated Quantum Dots by Resonant Raman Scattering. Journal of Nanoscience and Nanotechnology, 2008, 8, 789-794.	0.9	1
119	Grain size, texture, and crystallinity in lanthanum monosulfide thin films grown by pulsed laser deposition. Thin Solid Films, 2012, 524, 166-172.	1.8	1
120	Inelastic light scattering spectroscopy in Si/SiGe nanostructures: Strain, chemical composition and thermal properties. Solid State Communications, 2016, 245, 25-30.	1.9	1
121	Crystallinity, order, the thin-film silicon continuum, and the spectral dependence of the refractive index in thin silicon films grown through ultra-high-vacuum evaporation for a range of growth temperatures. Journal of Non-Crystalline Solids, 2021, 559, 120657.	3.1	1
122	Zeeman-ladder analysis of the Raman magnon energies in the quasi-one-dimensional antiferromagnet RbCoCl <sub>3</sub> . Physical Review B, 2022, 105, .	3.2	1
123	Qubit addressing using hyperfine-interaction control by an electric field in a magnetic crystal. Physical Review A, 2010, 82, .	2.5	0
124	One- and two-magnon and exciton Raman scattering in antiferromagnetic CoF <sub>2</sub> : Experiment and theory. Journal of the Korean Physical Society, 2013, 63, 817-820.	0.7	0
125	Dependence of spin dynamics on in-plane magnetic field in AlGaIn/GaN quantum wells. Europhysics Letters, 2015, 112, 67003.	2.0	0
126	An amorphous-to-crystalline phase transition within thin silicon films grown through ultra-high-vacuum evaporation on fused quartz substrates. MRS Advances, 2016, 1, 3257-3262.	0.9	0



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127	Direct-Gap Photoluminescence from a Si-Ge Multilayer Super Unit Cell Grown on Si <sub>0.4</sub> Ge <sub>0.6</sub> . ECS Journal of Solid State Science and Technology, 2018, 7, R115-R119.	1.8	0
128	Axial silicon-germanium nanowire heterojunctions: Structural properties and carrier transport. Journal of Applied Physics, 2019, 125, 205107.	2.5	0
129	Thin-film optical function acquisition from experimental measurements of the reflectance and transmittance spectra: a case study. Journal of Materials Science: Materials in Electronics, 2021, 32, 17033-17060.	2.2	0
130	Germanium Nanocrystal Properties from Photoluminescence. ECS Journal of Solid State Science and Technology, 2021, 10, 085003.	1.8	0
131	Light Emission from Germanium Nanostructures. Topics in Applied Physics, 2021, , 197-235.	0.8	0
132	Zero-wave-vector optical phonons in AgGaS <sub>2</sub> reexamined. Optical Materials, 2022, 128, 112325.	3.6	0